



BRIGHTTEK
BRIGHTTEK (EUROPE) LIMITED

Brighten up The World With LED!



ISO/TS 16949:2009



BS EN ISO 14001:2004



QC 90000 IECQ HSP98

PRODUCT DATASHEET

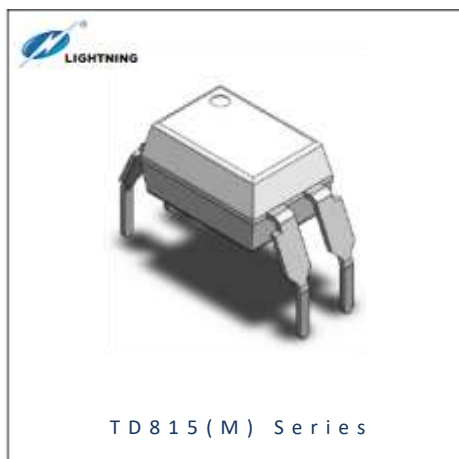


- ▶ DC Input Photo Coupler
- ▶ DIP4 Gullwing 400mil
- ▶ Darlington Transistor

TD815(M)-GV



Release Date: 07 July 2025 Version: A00



TD815(M) Series

DESCRIPTION:



The TD815(M) series combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar Darlington phototransistor detector in a plastic DIP4 package with Gullwing lead forming option.

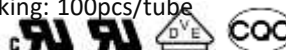
With the robust coplanar double mold structure, TD815(M) series provide the most stable isolation feature.

FEATURES:

APPLICATIONS:

- Sequence controller
- Telephone/FAX
- System appliances, measuring instrument
- Programmable logic controller

- High isolation 5000Vrms
- DC input with transistor output
- Operating temperature range -55°C to +110°C
- REACH & RoHS compliance; Halogen free
- MSL class 1
- Regulatory Approvals:
 - UL - UL1577
 - VDE - EN60747-5-5 (VDE0884-5)
 - CQC - GB4943.1, GB8898
 - cUL - CSA Component Acceptance Service Notice 5A
- Packing: 100pcs/tube



Partner with: LIGHTNING

NAMING & ORDERING INFORMATION:

Naming Information:

TD815 (M) - G V	
TD815	Part Number
M	Lead Form Option: DIP4 Gullwing
G	Green Option
V	VDE Option

Ordering Information:

TD815(M)-GV

Version No.	Original Release Date
Rev: A00	12/08/2024

SCHEMATIC DIAGRAM & MARKING:

Schematic Diagram:

PIN Definition	
1	Anode
2	Cathode
3	Emitter
4	Collector

Marking Information:

Marking Definition	
TD	Manufacturer Code
815	Part Number
V	VDE Applicable
Y	Fiscal Year
A	Manufacturing Code
WW	Work Week

Labelling Information:

 Part No.: XXXXXXXXXXXX Bin Code: X Lot No.: XXXXXXXX Date Code: XXXX QTY: XXX PCS MSL: 1 Made in Quanzhou Fujian 	This product is manufactured by  for Brighttek (Europe) Limited
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ABSOLUTE CHARACTERISTICS:

Absolute Maximum Ratings:

Parameter	Symbol	Ratings	Unit
INPUT			
Forward Current	I_F	60	mA
Peak Forward Current	I_{FP}	1 * ¹	A
Reverse Voltage	V_R	6	V
Input Power Dissipation	P_I	100	mW
OUTPUT			
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Collector Voltage	V_{ECO}	6	V
Collector Current	I_C	80	mA
Output Power Dissipation	P_O	150	mW
COMMON			
Total Power Dissipation	P_{tot}	200	mW
Isolation Voltage	V_{iso}	5000 * ²	Vrms
Operating Temperature	T_{opr}	-55~+110	°C
Storage Temperature	T_{stg}	-55~+125	°C
Soldering Temperature	T_{sol}	260 * ³	°C

*1. 100μs pulse, 100Hz frequency

*2. AC for 1 minute, R.H.=40~60%.

*3. For 10 seconds max.

ELECTRICAL CHARACTERISTICS:

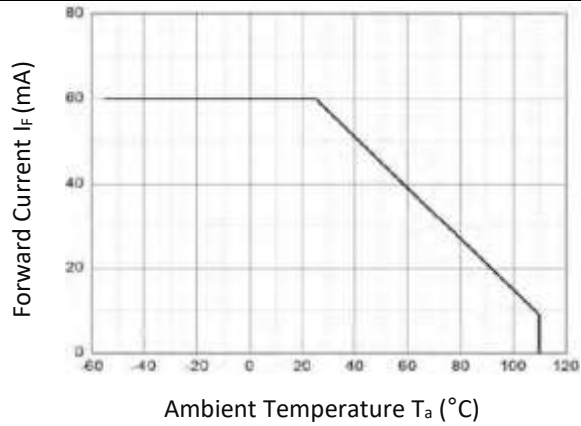
Electrical Optical Characteristics at $T_a=25^{\circ}\text{C}$:

Parameter	Symbol	Values			Unit	Test Condition
		Min.	Typ.	Max.		
INPUT						
Forward Voltage	V _F	---	1.24	1.4	V	I _F =10mA
Reverse Current	I _R	---	---	10	μA	V _R =6V
Input Capacitance	C _{IN}	---	10	---	pF	V=0, f=1kHz
OUTPUT						
Collector Dark Current	I _{CEO}	---	---	100	nA	V _{CE} =10V, I _F =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	40	---	---	V	I _C =0.1mA, I _F =0
Emitter-Collector Breakdown Voltage	BV _{ECO}	6	---	---	V	I _E =0.1mA, I _F =0
TRANSFER CHARACTERISTICS						
Current Transfer Ratio	CTR	600	---	7500	%	I _F =1mA, V _{CE} =2V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	---	0.8	1.0	V	I _F =20mA I _C =5mA
Isolation Resistance	R _{ISO}	10 ¹²	10 ¹⁴	---	Ω	DC=500V, 40~60% R.H.
Floating Capacitance	C _{IO}	---	0.4	1	pF	V=0, f=1MHz
Response Time (Rise)	t _r	---	95	300	μs	I _C =10mA, V _{CE} =2V R _L =100Ω
Response Time (Fall)	t _f	---	84	250	μs	I _C =10mA, V _{CE} =2V R _L =100Ω
Cutt-off Frequency	f _c	---	1	---	kHz	I _C =10mA, V _{CE} =2V R _L =100Ω, -3dB

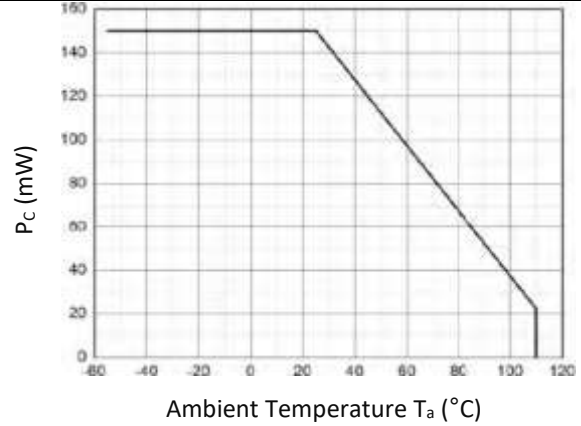
*1. Test voltage must be applied within dV/dt rating.

CHARACTERISTIC CURVES:

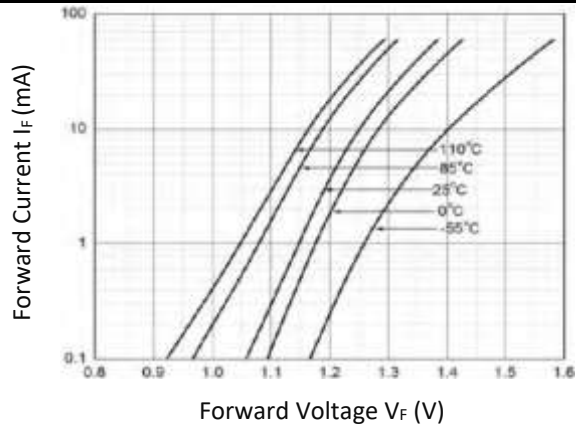
Forward Current v.s. Ambient Temperature



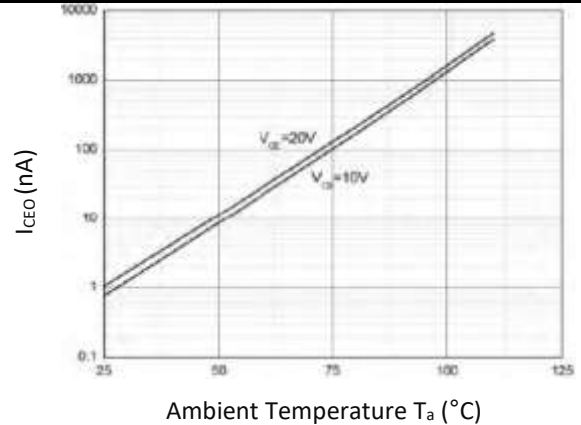
Collector Power Dissipation v.s. Ambient Temperature



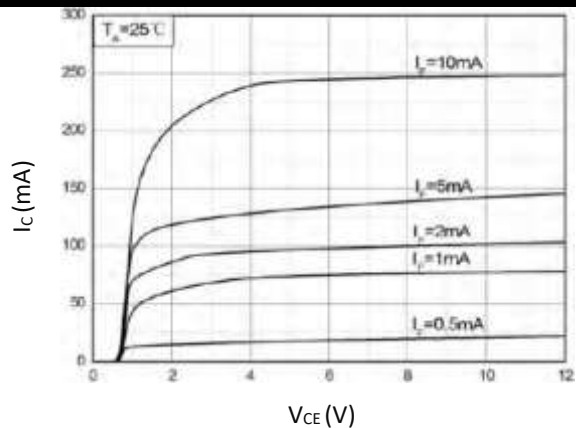
Forward Current v.s. Forward Voltage



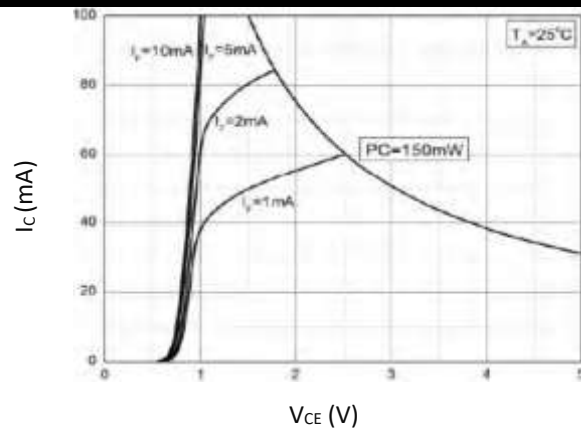
Collector Dark Current v.s. Ambient Temperature



Collect Current v.s. Collector-Emitter Voltage

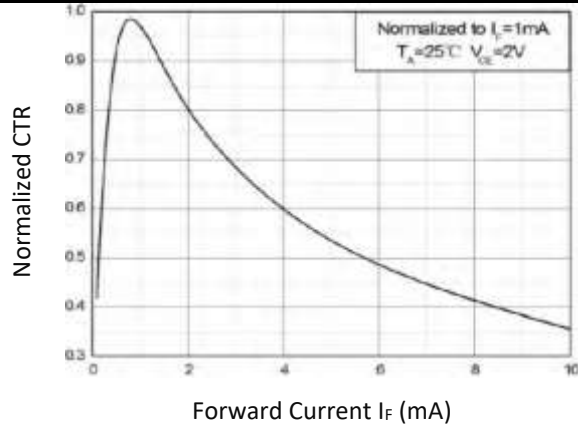


Collector Current v.s. Collector-Emitter Voltage

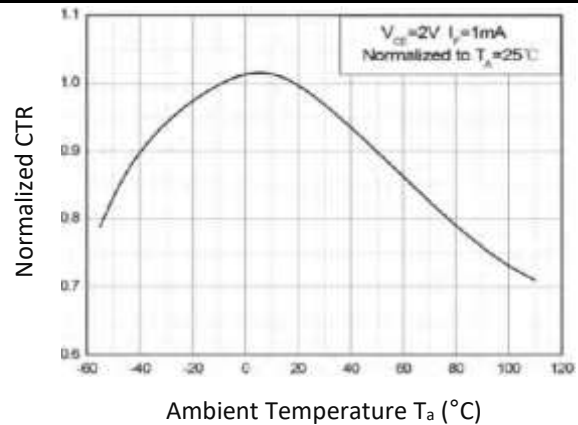


CHARACTERISTIC CURVES:

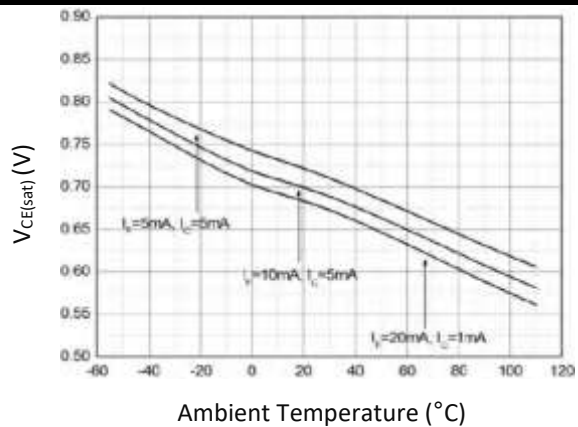
Normalized Current Transfer Ratio v.s. Forward Current



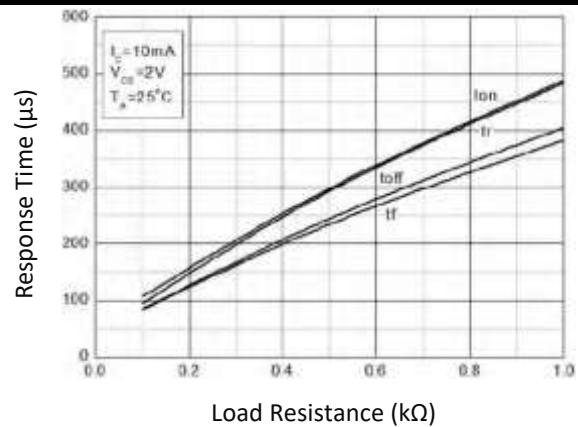
Normalized Current Transfer Ratio v.s. Ambient Temperature



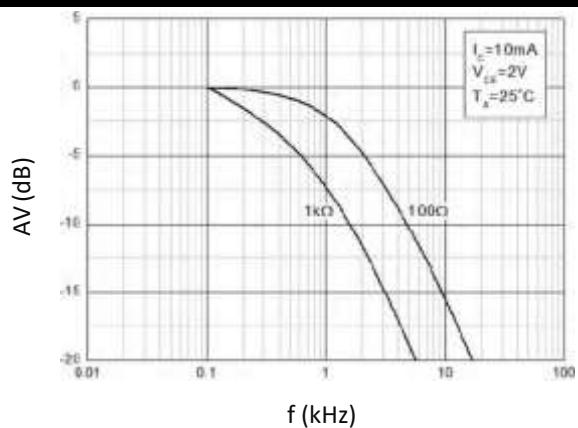
Collector-Emitter Saturation Voltage v.s. Ambient Temperature



Switching Time v.s. Load Resistance

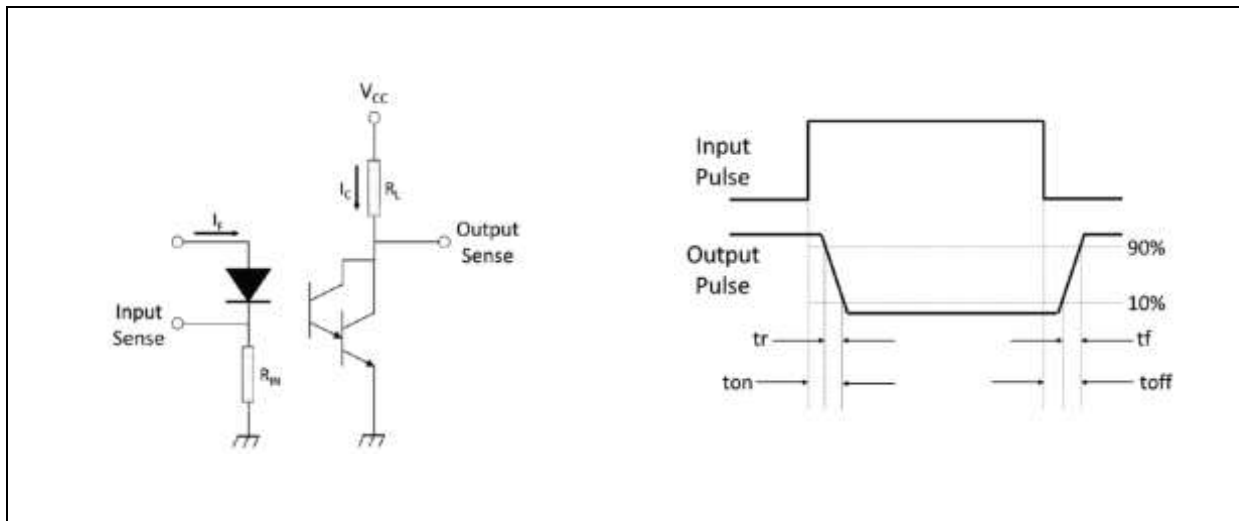


Frequency Response

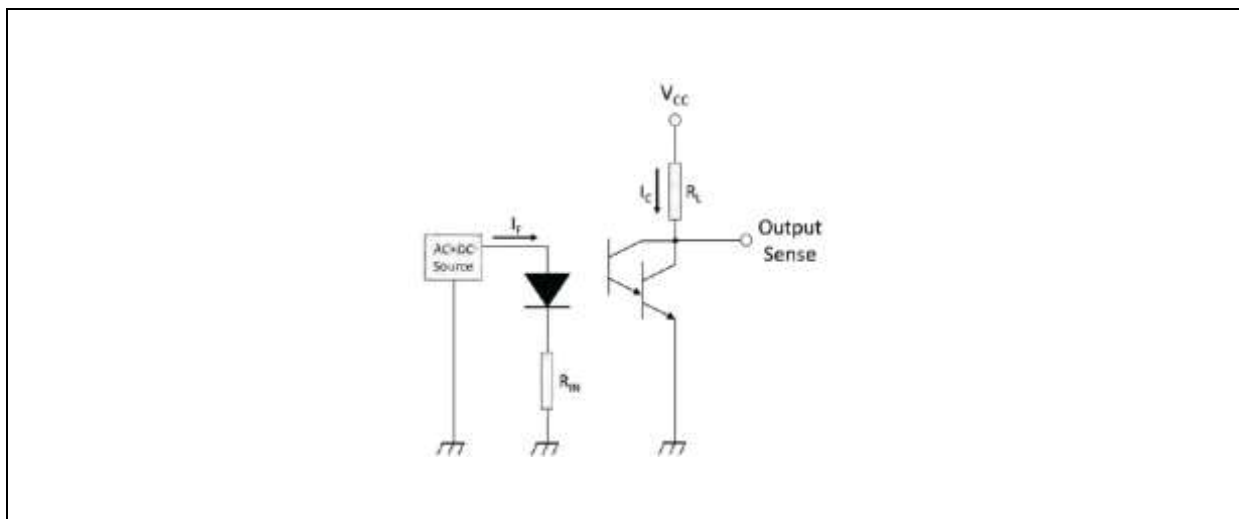


TEST CIRCUIT:

Test Circuit and Waveforms of Response Time:

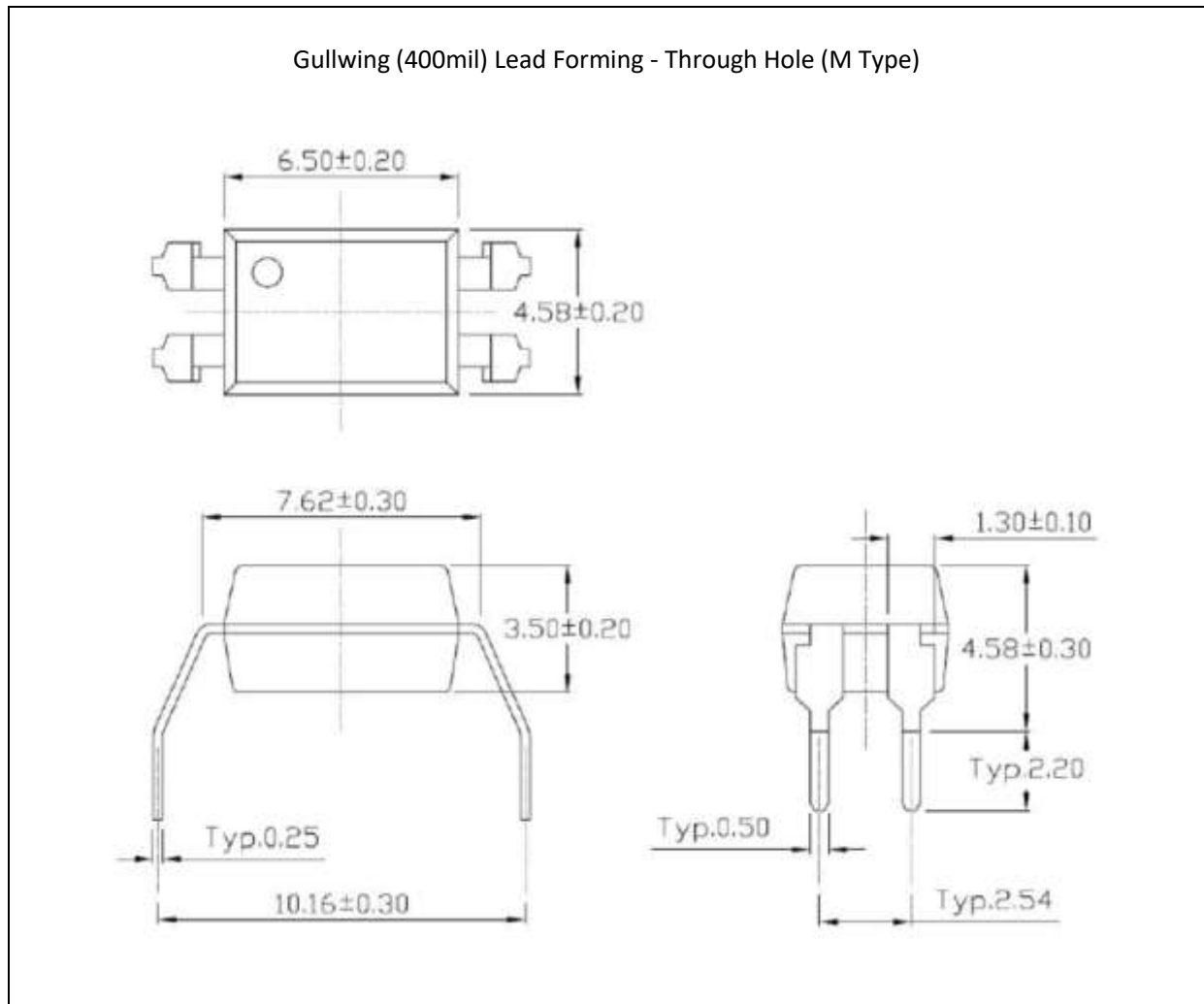


Test Circuit of Frequency Response:



OUTLINE DIMENSION:

Package Dimension:

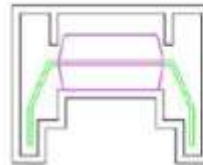
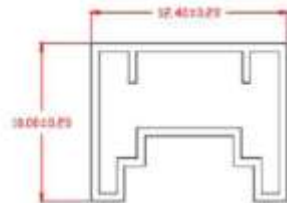


1. All dimensions are in millimetre (mm).

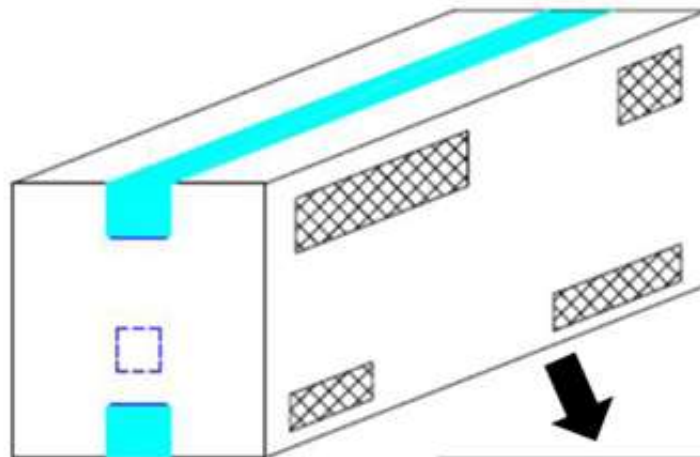
PACKING SPECIFICATION:

Tube Dimension:

100pcs/tube, 32 tube/inner box, 10 inner box (32Kpcs)/carton



● L x W x H = 52.5cm x 10.7cm x 4.7cm

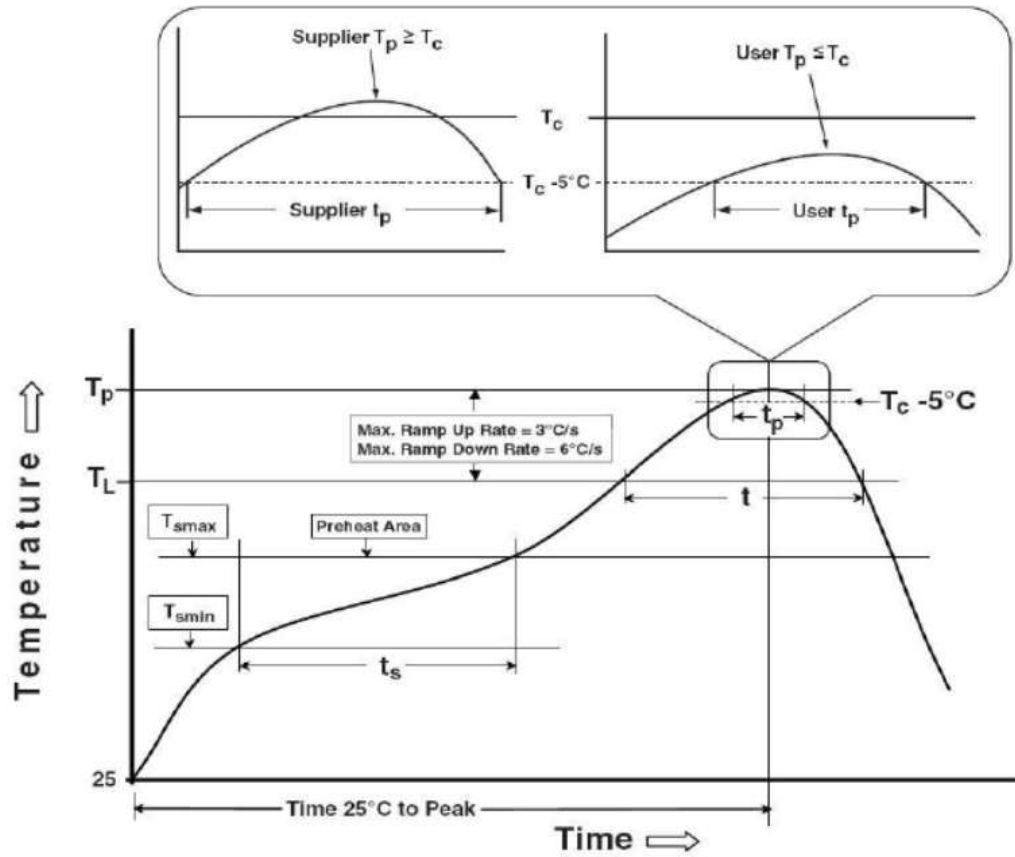


● L x W x H = 53.5cm x 23.5cm x 25.5cm



RECOMMENDED SOLDERING PROFILE:

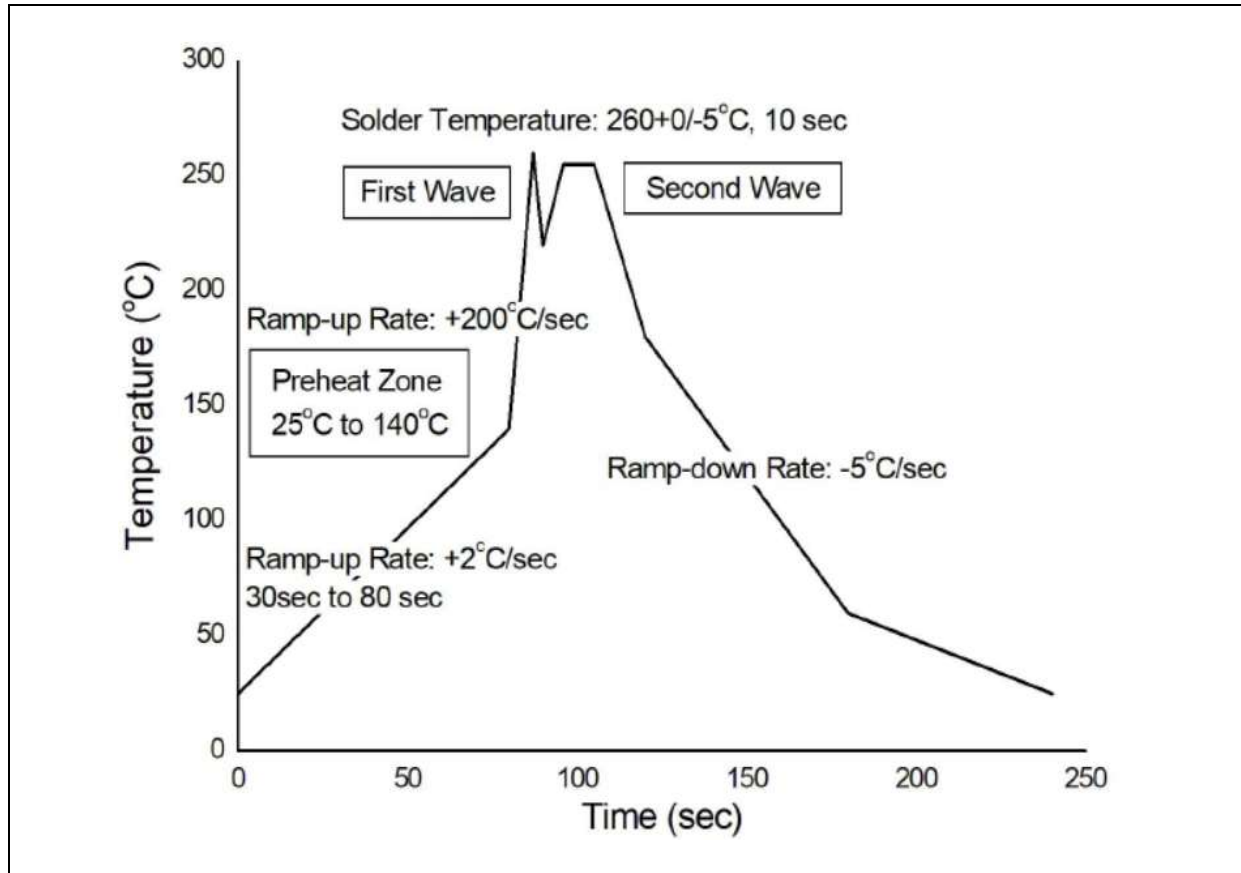
Reflow Information:



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T_{smin})	100°C	150°C
Temperature Max. (T_{smax})	150°C	200°C
Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds	60-120 seconds
Ramp-up Rate (t_L to t_p)	3°C/second max.	3°C/second max.
Liquidous Temperature (T_L)	183°C	217°C
Time (t_L) Maintained Above (T_L)	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235°C +0°C / -5°C	260°C +0°C / -5°C
Time (t_p) within 5°C of 260°C	20 seconds	30 seconds
Ramp-down Rate (T_p to T_L)	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

RECOMMENDED SOLDERING PROFILE:

Wave Soldering (JESD22-A111 Compliant):



Hand Soldering:

Soldering Temperature	$380 \pm 5^{\circ}\text{C}$
Soldering Time	3 sec max.

Note:

- One time soldering is recommended for all soldering methods.
- Do not solder more than three times for IR reflow soldering.